

Masaaki A Tanaka

List of Publications by Year in descending order

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docs citations

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times ranked

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citing authors

#	ARTICLE	IF	CITATIONS
1	Growth and characterization of quaternary-alloy ferromagnetic semiconductor (In,Ca,Fe)Sb. AIP Advances, 2022, 12, 015307.	1.3	1
2	Spin transport in fully ferromagnetic p-n junctions. Journal of Applied Physics, 2022, 131, 013902.	2.5	3
3	Theoretical analysis of the inverse Edelstein effect at the LaAlO ₃ /SrTiO ₃ interface with an effective tight-binding model: important role of the second d _{xy} subband. Applied Physics Express, 2022, 15, 013005.	2.4	3
4	Bias-dependent two-phase anisotropy in magnetoresistance of a GaMnAs-based magnetic tunnel junction. Applied Physics Express, 2022, 15, 033001.	2.4	1
5	Origin of perpendicular magnetic anisotropy in Co _x O ₄ thin films studied by x-ray magnetic circular and linear dichroism. Physical Review B, 2022, 105, .	3.2	3
6	Intervallence charge transfer and charge transport in the spinel ferrite ferromagnetic semiconductor Ru-doped Co ₂ O ₄ . Physical Review B, 2022, 105, .	3.2	3
7	Development of magnetism in Fe-doped magnetic semiconductors: Resonant photoemission and x-ray magnetic circular dichroism studies of (Ga,Fe)As. Physical Review B, 2022, 105, .	3.2	1
8	Gate-controlled proximity magnetoresistance in In ₂ O ₃ . Physical Review B, 2022, 105, .	3.2	1
9	Thickness-dependent quantum transport of Weyl fermions in ultra-high-quality SrRuO ₃ films. Applied Physics Letters, 2021, 118, 092408.	3.3	19
10	Structural and transport properties of highly Ru-deficient SrRu _{0.7} O ₃ thin films prepared by molecular beam epitaxy: Comparison with stoichiometric SrRuO ₃ . AIP Advances, 2021, 11, .	1.3	18
11	Minority-spin impurity band in n-type (In,Fe)As: A materials perspective for ferromagnetic semiconductors. Physical Review B, 2021, 103, .	3.2	9
12	Alternation of Magnetic Anisotropy Accompanied by Metal-Insulator Transition in Strained Ultrathin Manganite Heterostructures. Physical Review Applied, 2021, 15, .	3.8	4
13	Ferromagnetic Fe-doped InAs quantum dots with high Curie temperature. Applied Physics Express, 2021, 14, 083002.	2.4	0
14	Ferromagnetism and giant magnetoresistance in zinc-blende FeAs monolayers embedded in semiconductor structures. Nature Communications, 2021, 12, 4201.	12.8	5
15	Reduced magnetocrystalline anisotropy of CoFe ₂ O ₄ thin films studied by angle-dependent x-ray magnetic circular dichroism. AIP Advances, 2021, 11, 085317.	1.3	2
16	Recent progress in ferromagnetic semiconductors and spintronics devices. Japanese Journal of Applied Physics, 2021, 60, 010101.	1.5	24
17	Elemental Topological Dirac Semimetal In_2Te_3 with High Quantum Mobility. Advanced Materials, 2021, 33, e2104645.	21.0	12
18	Spin-orbit torque magnetization switching in a perpendicularly magnetized full Heusler alloy Co ₂ FeSi. AIP Advances, 2021, 11, .	1.3	1

#	ARTICLE	IF	CITATIONS
37	intrinsic spin-to-charge current conversion in an all-epitaxial single-crystal perovskite-oxide heterostructure of $\text{La}_{1-x}\text{Ca}_x\text{MnO}_3/\text{SrTiO}_3$. <i>Physical Review Letters</i> , 2020, 125, 077201.	3.6	23
38	Simultaneous Measurement of $\hat{\gamma}$ -ray and Conversion Electron Mössbauer Spectra of Fe Films under Total Reflection Conditions Using Synchrotron Mössbauer Source. <i>Journal of the Physical Society of Japan</i> , 2020, 89, 054707.	1.6	5
39	Current-induced linear motion of antiferromagnetically coupled skyrmion-like bubble domains stabilized without Dzyaloshinskii-Moriya interaction. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 435001.	2.8	2
40	Transport and magnetic properties of co-doped ferromagnetic semiconductor (In,Fe,Mn)As. <i>Applied Physics Express</i> , 2020, 13, 083005.	2.4	0
41	Electronic structure of the high- T_C ferromagnetic semiconductor (Ga,Fe)Sb: X-ray magnetic circular dichroism and resonance photoemission spectroscopy studies. <i>Physical Review B</i> , 2019, 100, .	3.2	16
42	Ultralow-Power Orbital-Controlled Magnetization Switching Using a Ferromagnetic Oxide Interface. <i>Physical Review Applied</i> , 2019, 12, .	3.8	3
43	Heavily Fe-doped ferromagnetic semiconductor (In,Fe)Sb with high Curie temperature and large magnetic anisotropy. <i>Applied Physics Express</i> , 2019, 12, 103004.	2.4	19
44	Giant gate-controlled proximity magnetoresistance in semiconductor-based ferromagnetic/non-magnetic bilayers. <i>Nature Physics</i> , 2019, 15, 1134-1139.	16.7	35
45	in the ferromagnetic semiconductor $\text{Ga}_{1-x}\text{Fe}_x\text{Sb}$		

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55	Large terahertz magnetization response in ferromagnetic nanoparticles. Applied Physics Letters, 2019, 114, .	3.3	8
56	Gate-controlled proximity magnetoresistance in an InAs / (Ga,Fe)Sb quantum well heterostructure. , 2019, , .		0
57	Si-based Spin Metal-Oxide-Semiconductor Field-Effect Transistors with an Inversion Channel. , 2019, , .		0
58	Current-induced motion of bubble domains stabilised in nanowires with edge defects. Journal Physics D: Applied Physics, 2019, 52, 025001.	2.8	6
59	Nearly ideal spin tunneling efficiency in $\text{Fe}/\text{MgO}/\text{Si}$ junctions. Physical Review Materials, 2019, 3, .	2.4	6
60	In-plane to perpendicular magnetic anisotropy switching in heavily-Fe-doped ferromagnetic semiconductor (Ga,Fe)Sb with high Curie temperature. Physical Review Materials, 2019, 3, .	2.4	15
61	Quantum size effect in an Fe quantum well detected by resonant tunneling carriers injected from a p -type Ge semiconductor electrode. Applied Physics Letters, 2018, 112, .	3.3	4
62	Spin transport and spin accumulation signals in Si studied in tunnel junctions with a Fe/Mg ferromagnetic multilayer and an amorphous SiO_xN_y tunnel barrier. Applied Physics Letters, 2018, 112, .	3.3	4
63	Electrical control of ferromagnetism in the n -type ferromagnetic semiconductor (In,Fe)Sb with high Curie temperature. Applied Physics Letters, 2018, 112, .	3.3	32
64	Large spin-valve effect in a lateral spin-valve device based on ferromagnetic semiconductor GaMnAs. Applied Physics Express, 2018, 11, 033003.	2.4	5
65	Electrical tuning of the band alignment and magnetoconductance in an n -type ferromagnetic semiconductor (In,Fe)As-based spin-Esaki diode. Applied Physics Letters, 2018, 112, .	3.3	6
66	Proximity-Induced Superconductivity in a Ferromagnetic Semiconductor (In,Fe)As. Journal of Physics: Conference Series, 2018, 969, 012036.	0.4	4
67	Impurity band conduction in group-IV ferromagnetic semiconductor $\text{Ge}_{1-x}\text{Fe}_x$ with nanoscale fluctuations in Fe concentration. Journal of Applied Physics, 2018, 124, 113902.	2.5	3
68	High-temperature ferromagnetism in new n -type Fe-doped ferromagnetic semiconductor (In,Fe)Sb. Applied Physics Express, 2018, 11, 063005.	2.4	37
69	Improved performance of a GaMnAs-based vertical spin electric double-layer transistor. Japanese Journal of Applied Physics, 2018, 57, 090301.	1.5	3
70	Intrinsic transmission magnetic circular dichroism spectra of GaMnAs. AIP Advances, 2018, 8, 035009.	1.3	2
71	Planar Nernst effect and Mott relation in (In,Fe)Sb ferromagnetic semiconductor. Journal of Applied Physics, 2018, 123, 175102.	2.5	3
72	Large current modulation and tunneling magnetoresistance change by a side-gate electric field in a GaMnAs-based vertical spin metal-oxide-semiconductor field-effect transistor. Scientific Reports, 2018, 8, 7195.	3.3	8

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73	Ultrafast magnetization modulation induced by the electric field component of a terahertz pulse in a ferromagnetic-semiconductor thin film. <i>Scientific Reports</i> , 2018, 8, 6901.	3.3	9
74	Cation distribution and magnetic properties in ultrathin $(\text{Ni}_{1-x}\text{Co}_x)\text{Fe}_2\text{O}_4$ ($x=0\text{--}1$) layers on Si(111) studied by soft x-ray magnetic circular dichroism. <i>Physical Review Materials</i> , 2018, 2, .	2.4	9
75	Electric-current-induced dynamics of bubble domains in a ferrimagnetic Tb/Co multilayer wire below and above the magnetic compensation point. <i>AIP Advances</i> , 2017, 7, .	1.3	10
76	Artificial control of the bias-voltage dependence of tunnelling-anisotropic magnetoresistance using quantization in a single-crystal ferromagnet. <i>Nature Communications</i> , 2017, 8, 15387.	12.8	12
77	Electronic structure and magnetic properties of magnetically dead layers in epitaxial $\text{Co}/\text{Fe}(\text{O})_2/\text{Co}$ heterostructures. <i>Physical Review B</i> , 2017, 95, 040401.	3.2	32
78	Origin of the large positive magnetoresistance of $\text{Co}/\text{Fe}(\text{O})_2/\text{Co}$ heterostructures. <i>Physical Review B</i> , 2017, 95, 040402.	3.2	10
79	Observation of the inverse spin Hall effect in the topological crystalline insulator SnTe using spin pumping. <i>Physical Review B</i> , 2017, 96, .	3.2	10
80	Hidden peculiar magnetic anisotropy at the interface in a ferromagnetic perovskite-oxide heterostructure. <i>Scientific Reports</i> , 2017, 7, 8715.	3.3	6
81	Magnetic anisotropy control by applying an electric field to the side surface of ferromagnetic films. <i>Scientific Reports</i> , 2017, 7, 5618.	3.3	18
82	Micromagnetic investigations of Néel- and Bloch-type skyrmion dynamics induced by spin Hall effect of cap layers. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 098001.	1.5	5
83	Inverse spin-valve effect in nanoscale Si-based spin-valve devices. <i>Journal of Applied Physics</i> , 2017, 122, .	2.5	5
84	Thickness dependence of Morin transition temperature in iridium-doped hematite layers studied through nuclear resonant scattering. <i>Hyperfine Interactions</i> , 2017, 238, 1.	0.5	8
85	Reduction of the magnetic dead layer and observation of tunneling magnetoresistance in $\text{La}_{0.67}\text{Sr}_{0.33}\text{MnO}_3$ -based heterostructures with a LaMnO_3 layer. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	12
86	Spin injection into silicon in three-terminal vertical and four-terminal lateral devices with $\text{Fe}/\text{Mg}/\text{MgO}/\text{Si}$ tunnel junctions having an ultrathin Mg insertion layer. <i>Physical Review B</i> , 2017, 96, .	3.2	24
87	Fe concentration dependence of tunneling magnetoresistance in magnetic tunnel junctions using group-IV ferromagnetic semiconductor GeFe. <i>AIP Advances</i> , 2017, 7, 105202.	1.3	1
88	Tunneling magnetoresistance in trilayer structures composed of group-IV-based ferromagnetic semiconductor $\text{Ge}_{1-x}\text{Sn}_x\text{Fe}_x$, MgO , and Fe. <i>Applied Physics Express</i> , 2016, 9, 123001.	2.4	3
89	Observation of Bi-Maxwellian Distributions in a H_2 Plasma Produced by a Narrow Gap VHF Discharge. <i>Plasma Processes and Polymers</i> , 2016, 13, 584-587.	3.0	1
90	Spin transport in nanoscale Si-based spin-valve devices. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	9

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91	Spin-dependent transport and current modulation in a current-in-plane spin-valve field-effect transistor. Applied Physics Letters, 2016, 109, 152403.	3.3	2
92	Sudden restoration of the band ordering associated with the ferromagnetic phase transition in a semiconductor. Nature Communications, 2016, 7, 12013.	12.8	15
93	High-temperature ferromagnetism in heavily Fe-doped ferromagnetic semiconductor (Ga,Fe)Sb. Applied Physics Letters, 2016, 108, .	3.3	94
94	Observation of spontaneous spin-splitting in the band structure of an n-type zinc-blende ferromagnetic semiconductor. Nature Communications, 2016, 7, 13810.	12.8	40
95	Vertical spin electric-double-layer transistor. , 2016, , .		0
96	High-temperature ferromagnetism in heavily Fe-doped ferromagnetic semiconductor (Ga,Fe)Sb. , 2016, , .		0
97	Room-temperature local ferromagnetism and its nanoscale expansion in the ferromagnetic semiconductor Ge _{1-x} Fe _x . Scientific Reports, 2016, 6, 23295.	3.3	20
98	Visible-light emission at room temperature in Mn-doped Si light-emitting diodes. Physical Review B, 2016, 93, .	3.2	2
99	Electronic structure near the Fermi level in the ferromagnetic semiconductor GaMnAs studied by ultrafast time-resolved light-induced reflectivity measurements. Physical Review B, 2016, 93, .	3.2	10
100	Mössbauer Analysis. Springer Series in Materials Science, 2016, , 341-352.	0.6	1
101	Magnetic properties and intrinsic ferromagnetism in $\text{Ga}_{1-x}\text{Mn}_x$ semiconductors. Physical Review B, 2015, 92, .		
102	Modulation of ferromagnetism in $\text{In}_{1-x}\text{Mn}_x$ wells via electrically controlled deformation of the electron wave functions. Physical Review B, 2015, 92, .	3.2	37
103	Growth and characterization of insulating ferromagnetic semiconductor (Al,Fe)Sb. Applied Physics Letters, 2015, 107, 232405.	3.3	34
104	Spin-dependent transport properties of a GaMnAs-based vertical spin metal-oxide-semiconductor field-effect transistor structure. Applied Physics Letters, 2015, 107, .	3.3	22
105	Effects of Digital Textbook-Based Nursing Education in Professional School. , 2015, , .		1
106	Origin of the broad three-terminal Hanle signals in $\text{Fe}/\text{SiO}_2/\text{Si}$ tunnel junctions. Applied Physics Letters, 2015, 107, 032407.	3.3	12
107	Memristive magnetic tunnel junctions with MnAs nanoparticles. Applied Physics Letters, 2015, 107, 122404.	3.3	2
108	Current-induced dynamics of bubble domains in perpendicularly magnetized TbFeCo wires. Applied Physics Express, 2015, 8, 073002.	2.4	13

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109	Intrinsic magneto-optical spectra of GaMnAs. Applied Physics Letters, 2015, 106, .	3.3	7
110	Improvement of saturation magnetization of Fe nanoparticles by post-annealing in a hydrogen gas atmosphere. Journal of Applied Physics, 2015, 117, .	2.5	26
111	Three-dimensional nanostructuring in YIG ferrite with femtosecond laser. Optics Letters, 2014, 39, 212.	3.3	10
112	Interplay between strain, quantum confinement, and ferromagnetism in strained ferromagnetic semiconductor (In,Fe)As thin films. Applied Physics Letters, 2014, 104, .	3.3	14
113	Annealing-induced enhancement of ferromagnetism and nanoparticle formation in the ferromagnetic semiconductor $\text{Ge}_{1-x}\text{Fe}_x$. Physical Review B, 2014, 90, .	3.2	17
114	Carrier transport properties of the Group-IV ferromagnetic semiconductor $\text{Ge}_{1-x}\text{Fe}_x$ with and without boron doping. AIP Advances, 2014, 4, .	1.3	10
115	High-field electroluminescence in semiconductor tunnel junctions with a Mn-doped GaAs layer. Journal of Applied Physics, 2014, 116, 113905.	2.5	2
116	Important role of the non-uniform Fe distribution for the ferromagnetism in group-IV-based ferromagnetic semiconductor GeFe. Journal of Applied Physics, 2014, 116, 173906.	2.5	9
117	Epitaxial growth and characterization of n-type magnetic semiconductor (In,Co)As. Japanese Journal of Applied Physics, 2014, 53, 04EM05.	1.5	3
118	DLC coating on a micro-trench by bipolar PBI&D and analysis of plasma behaviour. Journal Physics D: Applied Physics, 2014, 47, 335306.	2.8	4
119	Control of ferromagnetism by manipulating the carrier wavefunction in ferromagnetic semiconductor (In,Fe)As quantum wells. Applied Physics Letters, 2014, 104, 042404.	3.3	26
120	Visible-light electroluminescence in Mn-doped GaAs light-emitting diodes. Applied Physics Letters, 2014, 104, .	3.3	4
121	(Ga,Fe)Sb: A p-type ferromagnetic semiconductor. Applied Physics Letters, 2014, 105, .	3.3	43
122	Unveiling the impurity band induced ferromagnetism in the magnetic semiconductor (Ga,Mn)As. Physical Review B, 2014, 89, .	3.2	76
123	Recent progress in III-V based ferromagnetic semiconductors: Band structure, Fermi level, and tunneling transport. Applied Physics Reviews, 2014, 1, 011102.	11.3	96
124	Three-dimensional Nanostructuring in YIG Ferrite with Femtosecond Laser. , 2014, , .		0
125	Anomalous Fermi level behavior in GaMnAs at the onset of ferromagnetism. Applied Physics Letters, 2013, 103, 032411.	3.3	16
126	Studies on spintronics-related thin films using synchrotron-radiation-based Mössbauer spectroscopy. Hyperfine Interactions, 2013, 217, 127-135.	0.5	18

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127	Simulation analysis of triboplasma generation using the particle-in-cell/Monte Carlo collision (PIC/MCC) method. Journal Physics D: Applied Physics, 2012, 45, 495203.	2.8	8
128	Growth and characterization of n-type electron-induced ferromagnetic semiconductor (In,Fe)As. Applied Physics Letters, 2012, 101, .	3.3	78
129	Digging up bulk band dispersion buried under a passivation layer. Applied Physics Letters, 2012, 101, .	3.3	26
130	Effects of laser irradiation on the self-assembly of MnAs nanoparticles in a GaAs matrix. Applied Physics Letters, 2012, 101, .	3.3	3
131	Electron effective mass in n-type electron-induced ferromagnetic semiconductor (In,Fe)As: Evidence of conduction band transport. Applied Physics Letters, 2012, 101, .	3.3	51
132	Crystalline anisotropic magnetoresistance with two-fold and eight-fold symmetry in (In,Fe)As ferromagnetic semiconductor. Applied Physics Letters, 2012, 100, .	3.3	42
133	Spin-dependent tunneling transport in a ferromagnetic GaMnAs and un-doped GaAs double-quantum-well heterostructure. Applied Physics Letters, 2012, 100, .	3.3	8
134	Spintronics materials and devices - ferromagnetic semiconduc-tors and heterostructures. , 2012, , .		0
135	Magnetoresistance enhanced by inelastic cotunneling in a ferromagnetic MnAs nanoparticle sandwiched by nonmagnetic electrodes. Journal of Applied Physics, 2012, 111, 063716.	2.5	2
136	Valence-band structure of ferromagnetic semiconductor (In,Ga,Mn)As. Physical Review B, 2012, 86, .	3.2	20
137	Spintronics: Current Status and Future Prospects. Hyomen Kagaku, 2011, 32, 120-127.	0.0	1
138	Nearly non-magnetic valence band of the ferromagnetic semiconductor GaMnAs. Nature Physics, 2011, 7, 342-347.	16.7	128
139	Phase decomposition diagram of magnetic alloy semiconductor. Journal of Applied Physics, 2011, 109, 073919.	2.5	24
140	Structural and magnetic properties of Ge $_{1-x}$ Mnx thin films grown on Ge (001) substrates. Journal of Applied Physics, 2011, 110, 073903.	2.5	11
141	Synthesis of Biaryls and Oligoarenes Using Aryl[2-(hydroxymethyl)phenyl]dimethylsilanes. Bulletin of the Chemical Society of Japan, 2010, 83, 554-569.	3.2	45
142	Long spin-relaxation time in a single metal nanoparticle. Nature Nanotechnology, 2010, 5, 593-596.	31.5	49
143	Quantum-level control in a III-V-based ferromagnetic-semiconductor heterostructure with a GaMnAs quantum well and double barriers. Applied Physics Letters, 2010, 96, 052505.	3.3	15
144	Valence-Band Structure of the Ferromagnetic Semiconductor GaMnAs Studied by Spin-Dependent Resonant Tunneling Spectroscopy. Physical Review Letters, 2010, 104, 167204.	7.8	42

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145	Single-Crystalline Ferromagnetic Alloy Semiconductor $\text{Ge}_{1-x}\text{Mn}_x$ Grown on Ge(111). Applied Physics Express, 2010, 3, 123002.	2.4	7
146	Magneto-resistance of a Spin Metal-Oxide Semiconductor Field-Effect Transistor with Ferromagnetic MnAs Source and Drain Contacts. Japanese Journal of Applied Physics, 2010, 49, 113001.	1.5	21
147	Fluorescence photoswitching of a diarylethene- <i>perylenebisimide</i> dyad based on intramolecular electron transfer. Photochemical and Photobiological Sciences, 2010, 9, 181.	2.9	47
148	A New Spin-Functional Metal-Oxide Semiconductor Field-Effect Transistor Based on Magnetic Tunnel Junction Technology: Pseudo-Spin-MOSFET. Applied Physics Express, 2010, 3, 013003.	2.4	31
149	Investigation of InAlAs Oxide/InP Metal-Oxide Semiconductor Structures Formed by Wet Thermal Oxidation. Japanese Journal of Applied Physics, 2009, 48, 04C093.	1.5	5
150	In-Plane Uniaxial Magnetic Anisotropy of $[(\text{In}_y\text{Ga}_{1-y})_{1-x}\text{Mn}_x]\text{As}$ Characterized by Planar Hall Effect. Japanese Journal of Applied Physics, 2009, 48, 023001.	1.5	0
151	Germanium-Based Ferromagnetic Semiconductor $\text{Ge}_{1-x}\text{Fe}_x$ for Silicon Spintronics. ECS Transactions, 2009, 16, 953-960.	0.5	0
152	Electromotive force and huge magneto-resistance in magnetic tunnel junctions. Nature, 2009, 458, 489-492.	27.8	164
153	GaMnAs-based magnetic tunnel junctions with an AlMnAs barrier. Applied Physics Letters, 2009, 95, 242503.	3.3	29
154	Photocyclization Reaction of Diarylethene- <i>perylenebisimide</i> Dyads upon Irradiation with Visible (>500 nm) Light. Journal of Physical Chemistry C, 2009, 113, 11623-11627.	3.1	54
155	Planar Hall Effect and Magnetic Anisotropy in a Mn-doped GaAs/AlGaAs Heterostructure. IEEJ Transactions on Electrical and Electronic Engineering, 2008, 3, 394-398.	1.4	0
156	Magnetic anisotropy of ferromagnetic semiconductor $[(\text{InGa})\text{Mn}]\text{As}$ thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2901-2903.	0.8	1
157	Active oxygen generator by silent discharge and oxidation power in formation of oxide thin films. Electrical Engineering in Japan (English Translation of Denki Gakkai Ronbunshi), 2008, 163, 1-7.	0.4	0
158	Magneto-optical and magnetotransport properties of amorphous ferromagnetic semiconductor $\text{Ge}_{1-x}\text{Mn}_x$ thin films. Applied Physics Letters, 2008, 93, .	3.3	19
159	Epitaxial Growth and Magnetic Properties of Ferromagnetic Semiconductor $\text{Ge}_{1-x}\text{Fe}_x$ Thin Films Epitaxially Grown on Si(001) Substrates. Japanese Journal of Applied Physics, 2008, 47, 7108.	1.5	14
160	Invisible photochromism of diarylethene derivatives. Chemical Communications, 2008, , 3924.	4.1	46
161	Chapter 11 Properties and Functionalities of MnAs/III-V Hybrid and Composite Structures. Semiconductors and Semimetals, 2008, 82, 455-485.	0.7	1
162	Spin-valve effect by ballistic transport in ferromagnetic metal (MnAs)/semiconductor (GaAs) hybrid heterostructures. Physical Review B, 2008, 77, .	3.2	18

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163	Reconfigurable Logic Gates Using Single-Electron Spin Transistors. Japanese Journal of Applied Physics, 2007, 46, 6579-6585.	1.5	13
164	Tunneling Magnetoresistance in a Mn δ -doped GaAs/AlAs/MnAs Heterostructure. Japanese Journal of Applied Physics, 2007, 46, L755-L757.	1.5	0
165	Waveguide-Based 1.5 μ m Optical Isolator Based on Magneto-Optic Effect in Ferromagnetic MnAs. Japanese Journal of Applied Physics, 2007, 46, 205-210.	1.5	23
166	Structural and magnetic properties of epitaxially grown Ge $_{1-x}$ Fe $_x$ thin films: Fe concentration dependence. Applied Physics Letters, 2007, 90, 132512.	3.3	29
167	Magneto-optical and magnetotransport properties of heavily Mn-doped GaMnAs. Applied Physics Letters, 2007, 90, 112503.	3.3	56
168	Quantum size effect and tunneling magnetoresistance in ferromagnetic-semiconductor quantum heterostructures. Physical Review B, 2007, 75, .	3.2	62
169	Spin-dependent transport properties in GaMnAs-based spin hot-carrier transistors. Applied Physics Letters, 2007, 90, 162505.	3.3	20
170	A Silicon-Based Approach to Oligoarenes by Iterative Cross-Coupling Reactions of Halogenated Organo[(2-hydroxymethyl)phenyl]dimethylsilanes. Journal of the American Chemical Society, 2007, 129, 11694-11695.	13.7	84
171	Magnetic properties of MnAs nanoclusters embedded in a GaAs semiconductor matrix. Journal of Magnetism and Magnetic Materials, 2007, 310, 1932-1934.	2.3	25
172	Molecular beam epitaxy growth, magnetic and structural properties of MnAs thin films grown on InP(001) and InGaAsP. Journal of Crystal Growth, 2007, 301-302, 615-618.	1.5	3
173	Fabrication, structural and magnetic properties of InAlMnAs and InAlAs:MnAs granular thin films. Journal of Crystal Growth, 2007, 301-302, 627-630.	1.5	3
174	Schottky barrier MOSFETs with epitaxial ferromagnetic MnAs/Si(001) source and drain: Post-growth annealing and transport characteristics. Journal of Crystal Growth, 2007, 301-302, 611-614.	1.5	2
175	MOS-Based Spin Devices for Reconfigurable Logic. IEEE Transactions on Electron Devices, 2007, 54, 961-976.	3.0	98
176	Properties of Heavily Mn-doped GaMnAs with Curie Temperature of 172.5 K. Journal of Superconductivity and Novel Magnetism, 2007, 20, 417-420.	1.8	13
177	Intelligent Work-Study Support Based on Interactive Web Guide. Journal of Advanced Computational Intelligence and Intelligent Informatics, 2007, 11, 118-125.	0.9	0
178	Preparation and characterization of ferromagnetic DO3-phase Fe $_3$ Si thin films on silicon-on-insulator substrates for Si-based spin-electronic device applications. Applied Physics Letters, 2006, 89, 192503.	3.3	34
179	Magneto-optical properties of group-IV ferromagnetic semiconductor Ge $_{1-x}$ Fe $_x$ grown by low-temperature molecular beam epitaxy. Journal of Applied Physics, 2006, 99, 08D516.	2.5	35
180	Spin MOSFETs as a basis for spintronics. ACM Transactions on Storage, 2006, 2, 197-219.	2.1	35

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181	Epitaxial growth and magnetic properties of a new group-IV ferromagnetic semiconductor: Ge _{1-x} Fex. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006, 3, 4110-4114.	0.8	7
182	Spin polarized tunneling in III-V-based heterostructures with a ferromagnetic MnAs thin film and GaAs:MnAs nanoclusters. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 32, 416-418.	2.7	20
183	Schottky barrier height of ferromagnet/Si(001) junctions. <i>Applied Physics Letters</i> , 2006, 89, 072110.	3.3	20
184	Tunneling magnetoresistance of MnAs thin film/GaAs/AlAs/GaAs:MnAs nanoclusters and its AlAs barrier thickness dependence. <i>Applied Physics Letters</i> , 2006, 89, 242106.	3.3	21
185	Spintronics: recent progress and tomorrow's challenges. <i>Journal of Crystal Growth</i> , 2005, 278, 25-37.	1.5	48
186	Growth and magnetic properties of epitaxial MnAs/NiAs/MnAs heterostructures grown on exact GaAs(111)B substrates. <i>Journal of Crystal Growth</i> , 2005, 278, 649-654.	1.5	2
187	Precipitation of Amorphous Ferromagnetic Semiconductor Phase in Epitaxially Grown Mn-Doped Ge Thin Films. <i>Japanese Journal of Applied Physics</i> , 2005, 44, L1426-L1429.	1.5	52
188	A spin metal-oxide-semiconductor field-effect transistor (spin MOSFET) with a ferromagnetic semiconductor for the channel. <i>Journal of Applied Physics</i> , 2005, 97, 10D503.	2.5	48
189	Tunneling magnetoresistance in GaMnAs/AlAs/InGaAs/AlAs/GaMnAs double-barrier magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2005, 87, 012105.	3.3	32
190	Active Oxygen Species Generator by Low Pressure Silent Discharge and its Application to Water Treatment. <i>IEEJ Transactions on Fundamentals and Materials</i> , 2005, 125, 1017-1022.	0.2	2
191	Electrical and Optical Control of Ferromagnetism in III-V Semiconductor Heterostructures at High Temperature (~100 K). <i>Japanese Journal of Applied Physics</i> , 2004, 43, L233-L236.	1.5	44
192	Novel Reconfigurable Logic Gates Using Spin Metal-Oxide-Semiconductor Field-Effect Transistors. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 6032-6037.	1.5	53
193	Spin-Filter Transistor. <i>Japanese Journal of Applied Physics</i> , 2004, 43, L838-L841.	1.5	1
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